# United States Patent [19]

**Chittipeddi et al.**

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[54] **TRANSISTOR FABRICATION METHOD**


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[58] **Field of Search** ..... 437/41, 984, 913, 40, 437/29, 44; 148/DIG. 53



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[57] **ABSTRACT**

A method of forming a transistor is disclosed. Conventional fabrication techniques direct an ion implantation beam toward a substrate upon which a gate has already been formed. If the gate stack is too low relative to the incident beam energy, the dopant species may channel thorugh the gate stack, adversely affecting transistor performance. The present invention prevents channeling through this gate by covering the gate with a protective layer before ion implantation.


**2 Claims, 2 Drawing Sheets**